2SD1119

Silicon NPN epitaxial planar type

For low-frequency power amplification

■ Features

- Low collector-emitter saturation voltage V_{CE(sat)}
- Satisfactory operation performances at high efficiency with the lowvoltage power supply.
- Mini power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine

■ Absolute Maximum Ratings $T_a = 25$ °C

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Parameter	Symbol	Rating	Unit	3.0±0.15			
Collector-base voltage (Emitter open)	V_{CBO}	40	V				
Collector-emitter voltage (Base open)	V_{CEO}	25	V				
Emitter-base voltage (Collector open)	V_{EBO}	7	V				
Collector current	I_C	3	A	2			
Peak collector current	I_{CP}	5	A	Marking Symbol: T			
Collector power dissipation *	P_{C}	1	W	xes o			
Junction temperature	T_{j}	150	°C	18,181			
Storage temperature	T _{stg}	-55 to +150	°C	all uso			
Note) *: Printed circuit board: Copper foil area of 1 cm ² or more, and the							
board thickness of 1.7 mm for the collector portion							
			.0				
■ Electrical Characteristics T _a = 25°C ± 3°C							
Electrical orial actensities $T_a = 23 \text{ C} \pm 3 \text{ C}$							
			. 63	<i>U</i>			

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

Unit: mm 1.5±0.1 2: Collector MiniP3-F1 Package

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

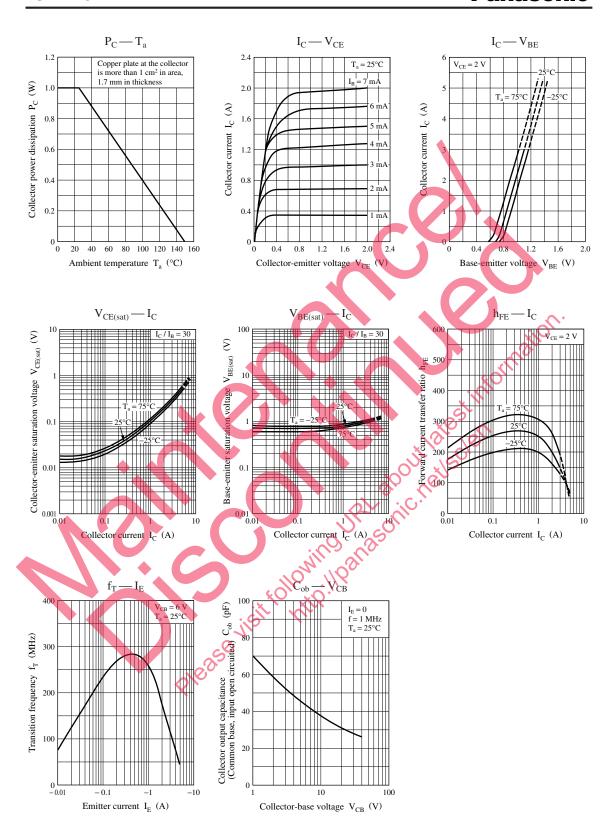
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	25			V
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	$I_{\rm E} = 10 \mu \text{A}, I_{\rm C} = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 10 \text{ V}, I_E = 0$			0.1	μΑ
Forward current transfer ratio *1	h _{FE1} *3	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}$	230		600	_
	hFE2	$V_{CE} = 2 \text{ V}, I_{C} = 2 \text{ A}$	150			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = 3 A, I_B = 0.1 A$			1	V
Transition frequency	f_T	$V_{CB} = 6 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 20 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$			50	pF
(Common base, input open circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R
$h_{\rm FE1}$	230 to 380	340 to 600



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